HS-0546RH, HS-0547RH

Radiation Hardened Single 16/Differential 8 Channel CMOS Analog Multiplexers with Active Overvoltage Protection

FN3544
Rev.4.00
March 13, 2006

The HS-0546RH and HS-0547RH are radiation hardened analog multiplexers with Active Overvoltage Protection and guaranteed r_{ON} matching. Analog input levels may greatly exceed either power supply without damaging the device or disturbing the signal path of other channels. Active protection circuitry assures that signal fidelity is maintained even under fault conditions that would destroy other multiplexers. Analog inputs can withstand constant 70V peak-to-peak levels with ±15V supplies and digital inputs will sustain continuous faults up to 4V greater than either supply. In addition, signal sources are protected from short circuiting should multiplexer supply loss occur: each input presents 1kΩ of resistance under this condition. These features make the HS-0546RH and HS-0547RH ideal for use in systems where the analog inputs originate from external equipment or separately powered circuitry. Both devices are fabricated with 44V dielectrically isolated CMOS technology. The HS-0546 is a 16 channel device and the HS-0547 is an 8 channel differential version. If input overvoltage protection is not needed, the HS-0506 and HS-0507 multiplexers are recommended.

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed here must be used when ordering.

Detailed Electrical Specifications for these devices are contained in SMD 5962-95693. A "hot-link" is provided on our homepage for downloading.
http://www.intersil.com

Features

- Electrically Screened to SMD # 5962-95693
- QML Qualified per MIL-PRF-38535 Requirements
- Gamma Dose . . . . . 1 x 10^4RAD(Si)
- No Latch-Up
- No Channel Interaction During Overvoltage
- Guaranteed r_{ON} Matching
- Maximum Power Supply 44V
- Break-Before-Make Switch
- Analog Signal Range. . . . . .±15V
- Access Time. 1.0µs

Applications

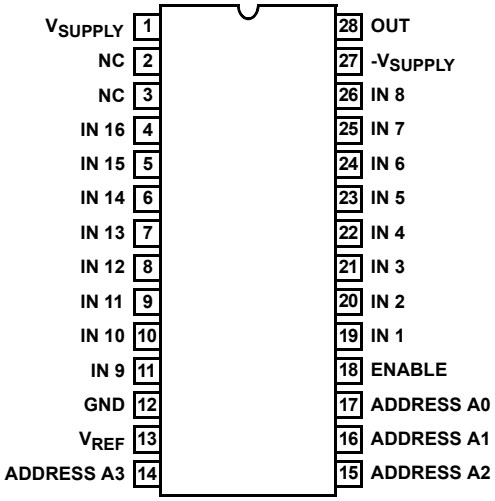
- Data Acquisition Systems
- Control Systems
- Telemetry

Ordering Information

ORDERING NUMBER	INTERNAL MKT. NUMBER	PART MARKING	TEMP. RANGE (°C)
5962D9569301V9A	HS0-0546RH-Q	Q-5962D9569301V9A	25
5962D9569301VXC	HS1B-0546RH-Q	Q-5962D9569301VXC	-55 to 125
5962D9569302V9A	HS0-0547RH-Q	Q-5962D9569302V9A	25
5962D9569302VXC	HS1B-0547RH-Q	Q-5962D9569302VXC	-55 to 125

Pinouts

HS-0546RH GDIP1-T28 (CERDIP) OR CDIP2-T28 (SBDIP)
TOP VIEW



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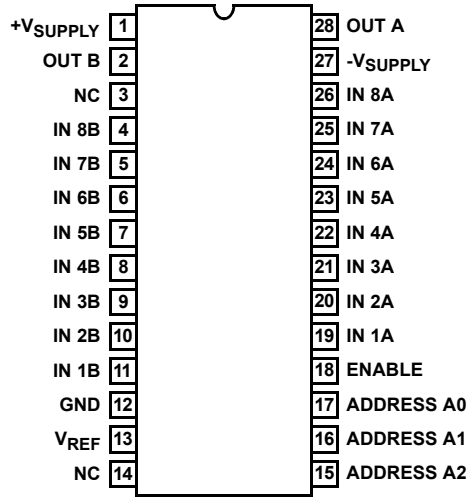
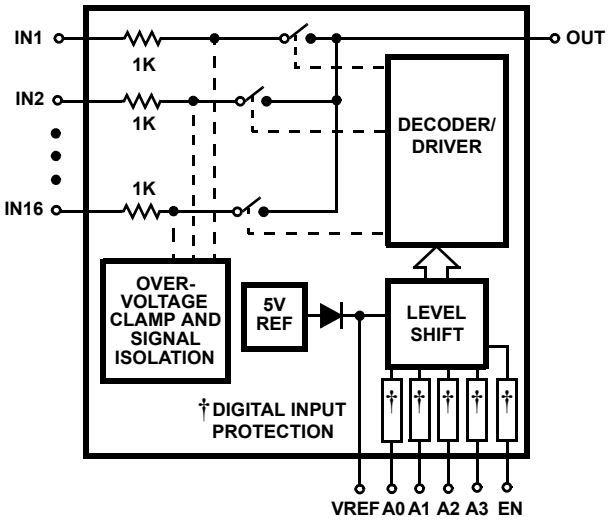
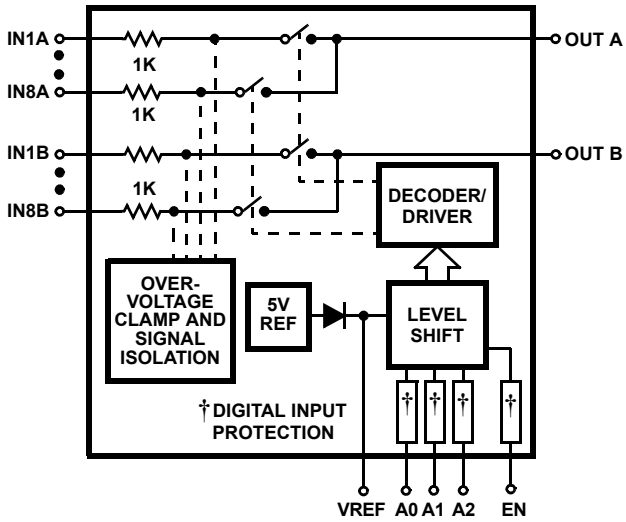


Functional Diagrams

HS-0546RH



HS-0547RH



HS-0546RH TRUTH TABLE

A3	A2	A1	A0	EN	"ON" CHANNEL
X	X	X	X	L	NONE
L	L	L	L	H	1
L	L	L	H	H	2
L	L	H	L	H	3
L	L	H	H	H	4
L	H	L	L	H	5
L	H	L	H	H	6
L	H	H	L	H	7
L	H	H	H	H	8
H	L	L	L	H	9
H	L	L	H	H	10
H	L	H	L	H	11
H	L	H	H	H	12
H	H	L	L	H	13
H	H	L	H	H	14
H	H	H	L	H	15
H	H	H	H	H	16

HS-0547RH TRUTH TABLE

A2	A1	A0	EN	"ON" CHANNEL PAIR
X	X	X	L	NONE
L	L	L	H	1
L	L	H	H	2
L	H	L	H	3
L	H	H	H	4
H	L	L	H	5
H	L	H	H	6
H	H	L	H	7
H	H	H	H	8

Switching Waveforms

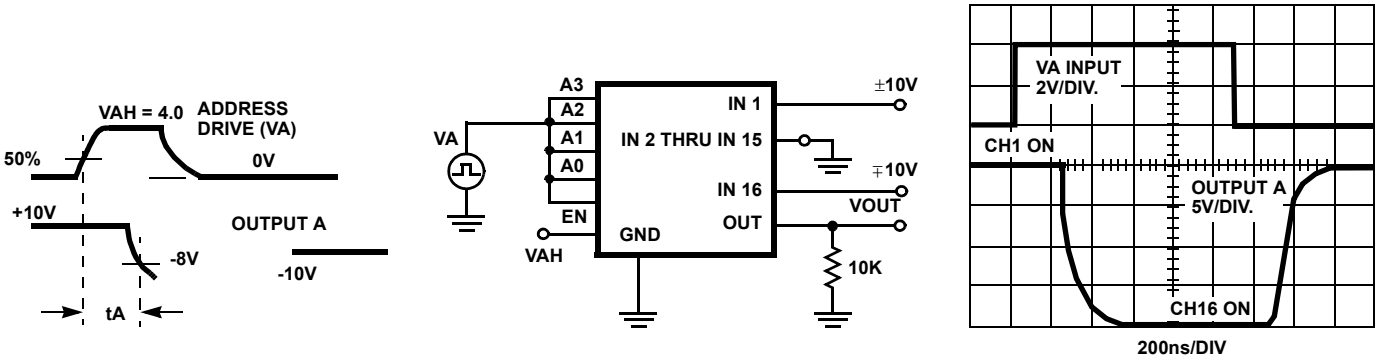


FIGURE 1. ACCESS TIME

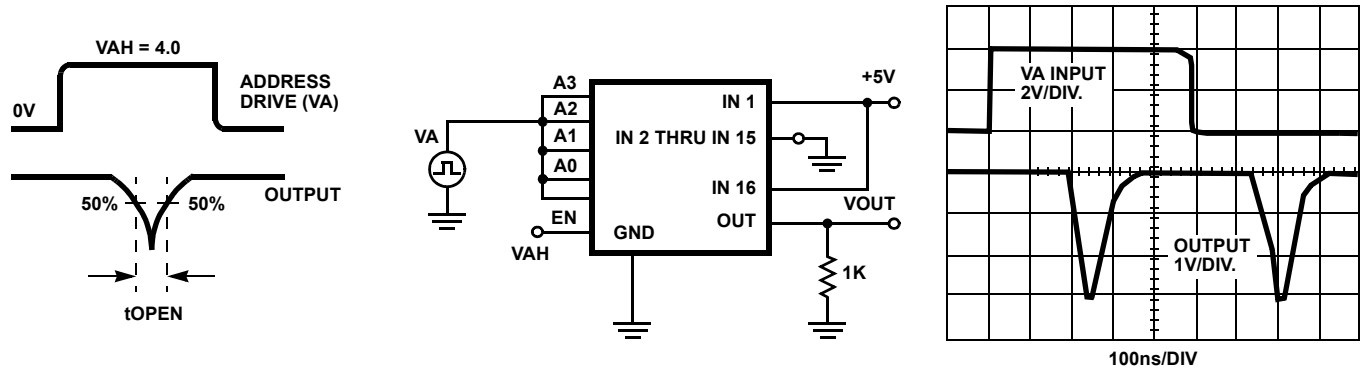


FIGURE 2. BREAK-BEFORE-MAKE DELAY (tOPEN)

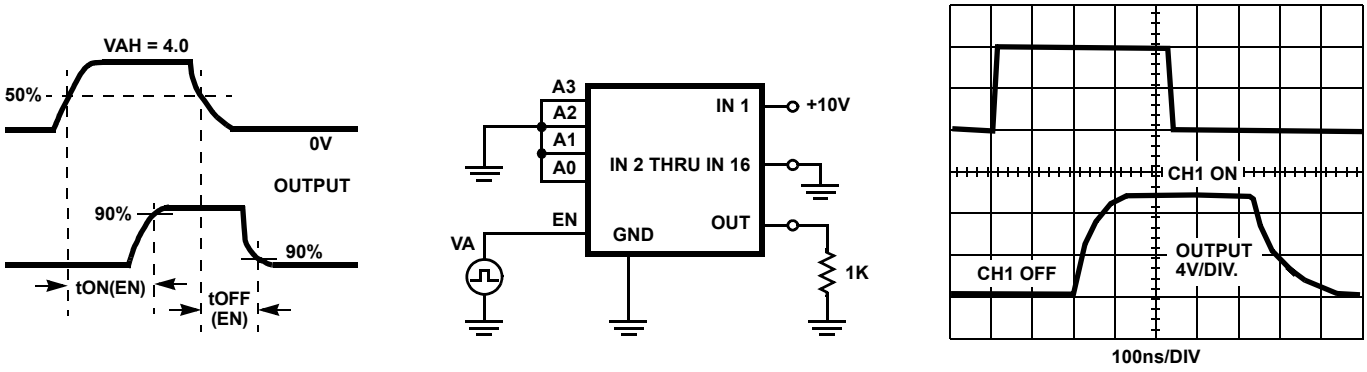


FIGURE 3. ENABLE DELAY tON(EN), tOFF(EN)

Schematic Diagrams

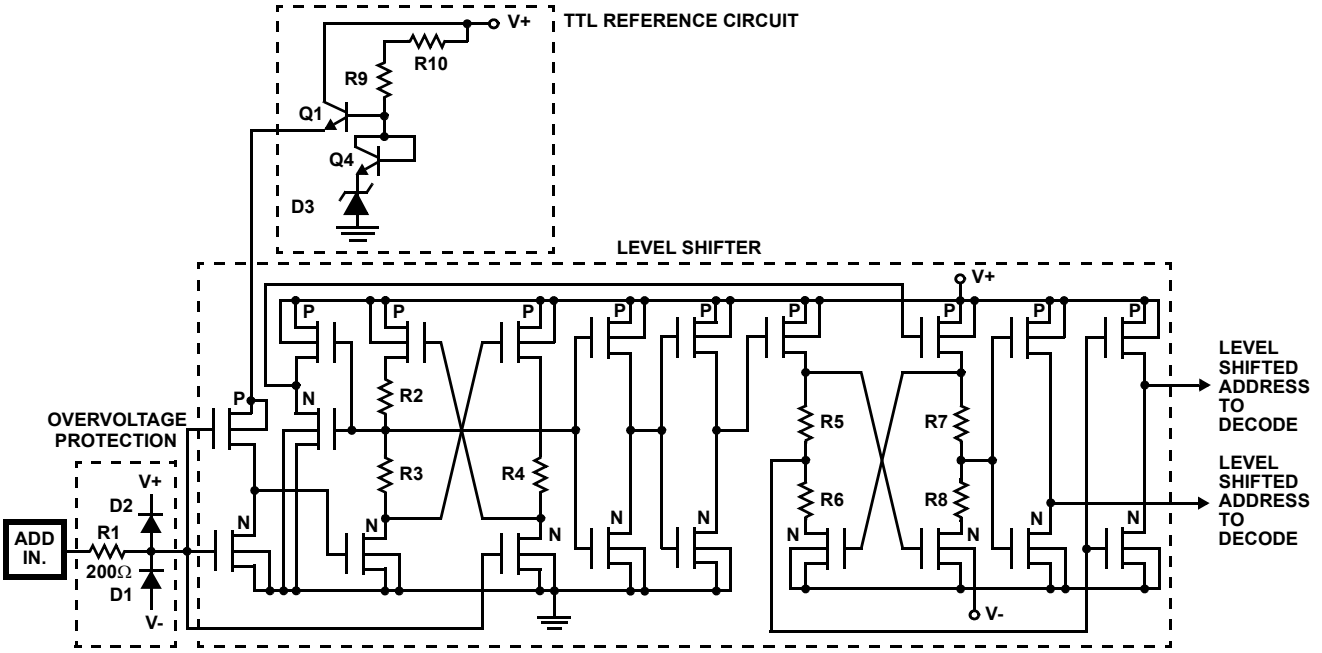


FIGURE 4. ADDRESS INPUT BUFFER AND LEVEL SHIFTER

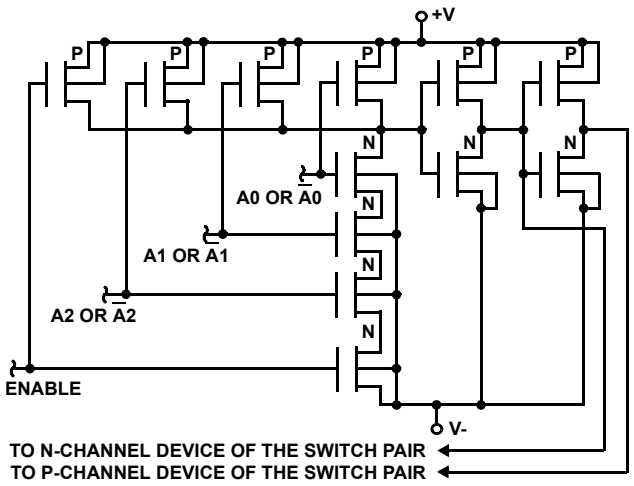


FIGURE 5. ADDRESS DECODER

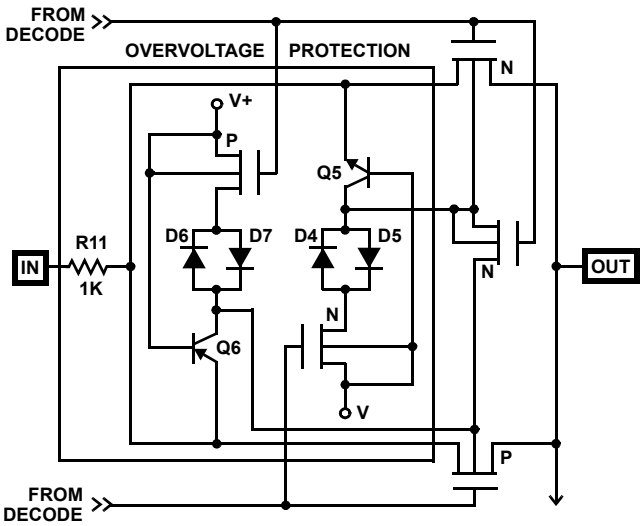
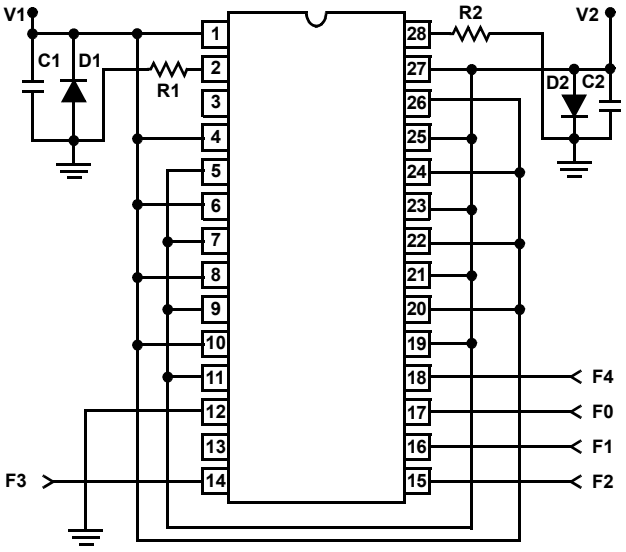


FIGURE 6. MULTIPLEX SWITCH

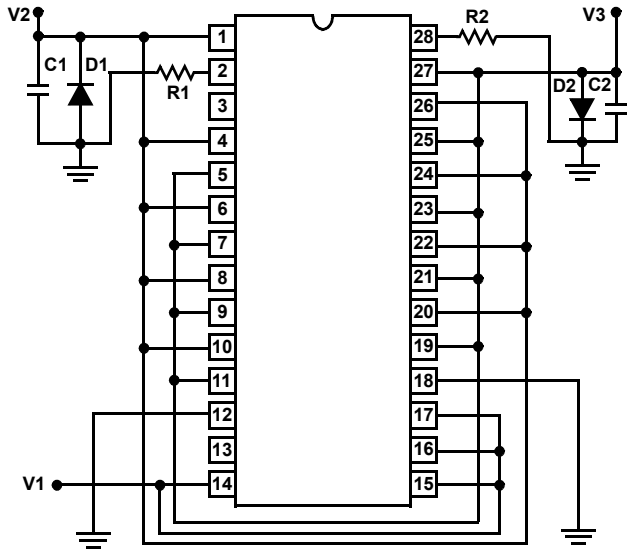
Burn-In/Life Test Circuits



DYNAMIC AND LIFE TEST

NOTES:

1. The Dynamic Test Circuit is utilized for all life testing.
2. V1 = +15V minimum, +16V maximum.
3. V2 = -15V maximum, -16V minimum.
4. R1, R2 = 10kΩ, ±5%, 1/4 or 1/2W (per socket).
5. C1, C2 = 0.01μF minimum (per socket) or 0.1μF minimum (per row).
6. D1, D2 = 1N4002 or equivalent (per board).
7. F0 = 100kHz, 10%; F1 = F0/2; F2 = F1/2; F3 = F2/2; F4 = F3/2 40% - 60% duty cycle; VIL = 0.8V maximum; VIH = 4.0V minimum.

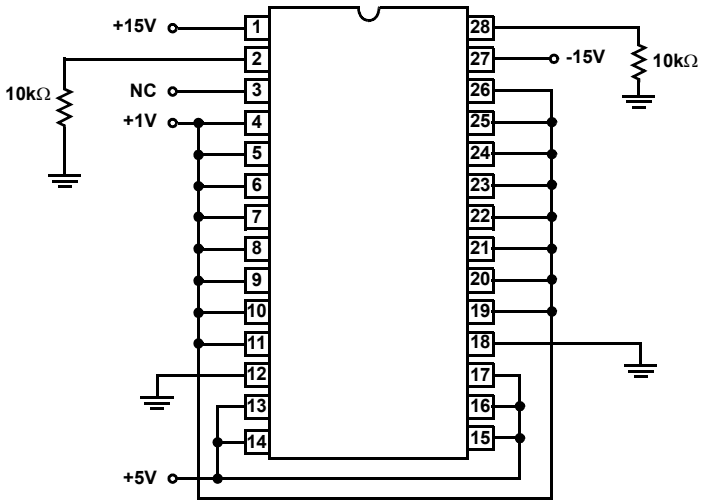


STATIC

NOTES:

8. V1 = +5V minimum, +6V maximum.
9. V2 = +15V minimum, +16V maximum.
10. V3 = -15V maximum, -16V minimum.
11. R1, R2 = 10kΩ, ±5%, 1/4 or 1/2W (per socket).
12. C1, C2 = 0.01μF minimum (per socket) or 0.1μF minimum (per row).
13. D1, D2 = 1N4002 or equivalent (per board).

Irradiation Circuit



Die Characteristics

DIE DIMENSIONS:

83.9 mils x 159 mils x 19 mils

INTERFACE MATERIALS:

Glassivation:

Type: Nitride
Thickness: 7kÅ ±0.7kÅ

Top Metallization:

Type: Al
Thickness: 16kÅ ±2kÅ

Substrate:

CMOS, DI

ASSEMBLY RELATED INFORMATION:

Substrate Potential:

Unbiased (DI)

ADDITIONAL INFORMATION:

Worst Case Current Density:

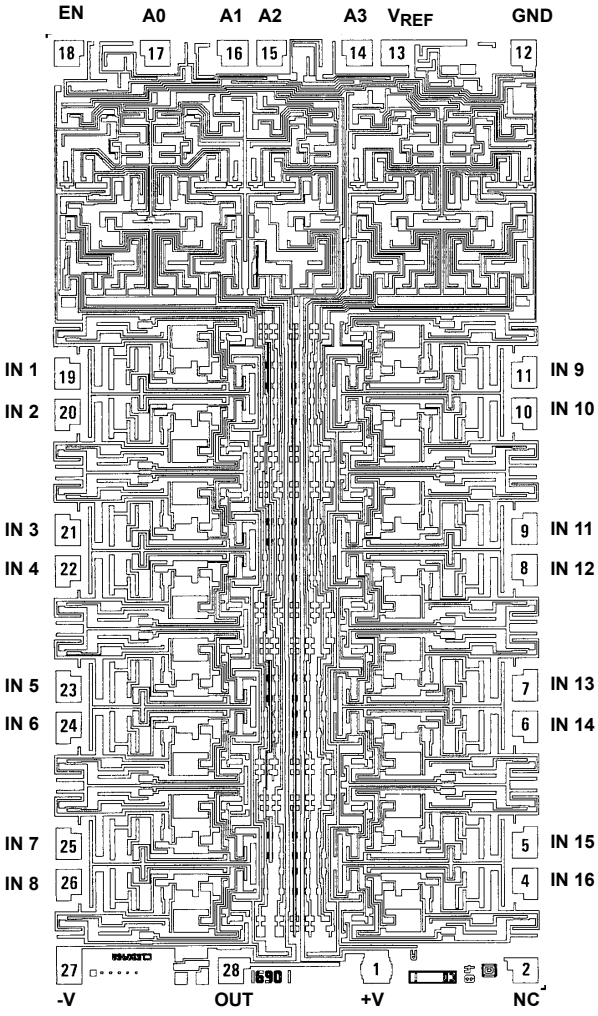
1.4×10^5 A/cm^2

Transistor Count:

HS-0546 - 485
HS-0547 - 485

Metallization Mask Layout

HS-0546RH



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